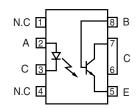
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Optocoupler, Phototransistor Output, with Base Connection



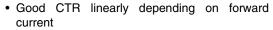


DESCRIPTION

The IL352 optically coupled isolator that features a high current transfer ratio, low coupling capacitance and high isolation voltage. It has a GaAs infrared emitting diode emitter, which is optically coupled to a silicon planar phototransistor detector. The component is housed in a thin line package.

The coupling device is designed for signal transmission between two electrically separated circuits. The potential difference between the circuits to be coupled must not exceed the maximum permissible reference voltages.

FEATURES





- Isolation test voltage: 3000 V_{RMS}
- High collector emitter voltage, V_{CEO} = 30 V
- · Low saturation voltage
- Fast switching times
- r dot owntorming times
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

AGENCY APPROVALS

- UL1577, file no. E52744 system code S
- DIN EN 60747-5-5 (VDE 0884) available with option 1

ORDER INFORMATION					
PART	REMARKS				
IL352	CTR > 100 %, SMD-8				

ABSOLUTE MAXIMUM RATINGS (1)							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
INPUT							
Reverse voltage		V_{R}	6	V			
DC forward current		I _F	60	mA			
Total power dissipation		P _{diss}	50	mW			
Derate linearly from 25 °C			0.66	mW/°C			
OUTPUT							
Collector emitter voltage		V _{CE}	70	V			
Emitter base voltage		V _{EBO}	7	V			
Callantan annuant		Ic	50	mA			
Collector current	t ≤ 1 ms	I _C	100	mA			
Total power dissipation		P _{diss}	150	mW			
Derate linearly from 25 °C			2.5	mW/°C			
COUPLER							
Isolation test voltage between emitter and detector	t = 1.0 s	$V_{\rm ISO}$	3000	V_{RMS}			
	V _{IO} = 500 V, T _{amb} = 25 °C	R _{IO}	≥ 10 ¹²	Ω			
Isolation resistance	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	≥ 10 ¹¹	Ω			
Storage temperature range		T _{stg}	- 40 to + 150	°C			
Ambient temperature range		T _{amb}	- 40 to + 85	°C			
Junction temperature		T _i	100	°C			
Soldering temperature (2)	max. 10 s, dip soldering: distance to seating plane ≥ 1.5 mm	T _{sld}	260	°C			

Notes

 $T_{amb} = 25 \, ^{\circ}C$, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

 $[\]ensuremath{^{(2)}}$ Refer to reflow profile for soldering conditions for surface mounted devices.



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ELECTRICAL CHARACTERISTCS								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
INPUT								
Forward voltage	I _F = 10 mA		V _F		1.3	1.5	٧	
Reverse current	V _R = 6 V		I _R		0.1	10	μΑ	
Capacitance	V _R = 0 V, f = 1.0 MHz		Co		25		pF	
OUTPUT								
Collector emitter breakdown voltage	$I_C = 1 \text{ mA}, I_E = 100 \mu\text{A}$		BV _{CEO}	30			V	
Emitter collector breakdown voltage	$I_C = 1 \text{ mA}, I_E = 100 \mu\text{A}$		BV _{ECO}	7			V	
Collector emitter leakens august	$V_{CE} = 10 \text{ V}, I_F = 0, T_A = 25 ^{\circ}\text{C}$		I _{CEO}		5	50	nA	
Collector emitter leakage current	$V_{CE} = 30 \text{ V}, I_F = 0, T_A = 85 ^{\circ}\text{C}$		I _{CEO}			500	μΑ	
Collector base breakdown voltage	I _C = 100 μA		BV _{CBO}	70			٧	
Collector emitter capacitance	$V_{CE} = 0$		C _{CE}		6		pF	
COUPLER								
Saturation voltage collector emitter	$I_F = 10 \text{ mA}, I_C = 0.5 \text{ mA},$		V_{CEsat}	•		0.3	٧	
Collector emitter capacitance	V _{CE} = 0		C _{CE}		6		pF	
Capacitance (input to output)	f = 1 MHz		C _{IO}		0.5		pF	

Note

 T_{amb} = 25 $^{\circ}C,$ unless otherwise specified.

Minimum and maximum values were tested requierements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
DC current transfer ratio	$I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V}$		CTR _{DC}	100			%
	$I_F = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$		CTR _{DC}	34			%

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Switching time, non-saturated	I_C = 2 mA, R_E = 100 Ω , V_{CC} = 10 V, $RH \le$ 50 %	t _{on} , t _{off}		10		μs	

TYPICAL CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

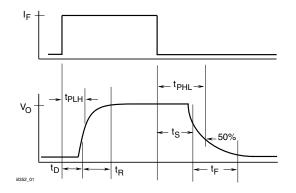


Fig. 1 - Switching Waveform

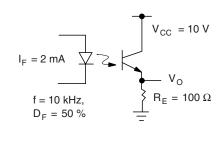


Fig. 2 - Switching Schematic

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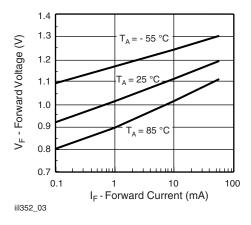


Fig. 3 - Forward Voltage vs. Forward Current

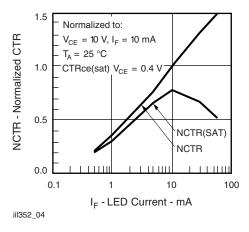


Fig. 4 - Normalized Non-Saturated and Saturated CTR vs. LED Current

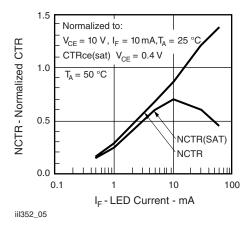


Fig. 5 - Normalized Non-Saturated and Saturated CTR vs. LED Current

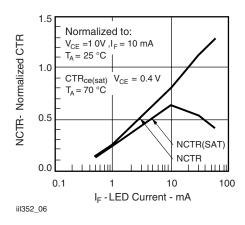
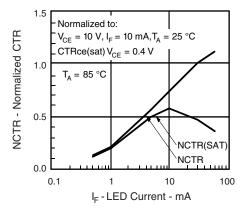


Fig. 6 - Normalized Non-Saturated and Saturated CTR vs. LED Current



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Fig. 7 - Normalized Non-Saturated and Saturated CTR vs. LED Current

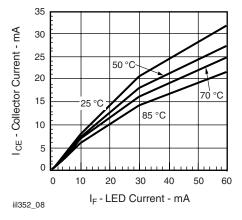


Fig. 8 - Collector Emitter Current vs. Temperature and LED Current



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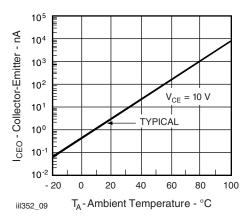


Fig. 9 - Collector Emitter Leakage Current vs.Temperature

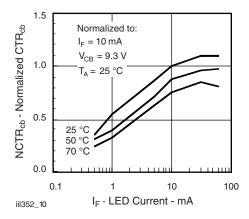


Fig. 10 - Normalized CTR_{cb} vs. LED Current and Temperature

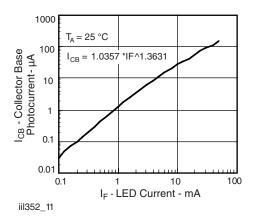


Fig. 11 - Collector Base Photocurrent vs. LED Current

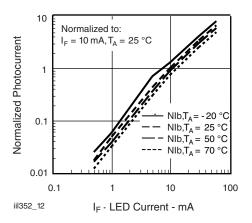


Fig. 12 - Normalized Photocurrent vs. I_F and Temperature

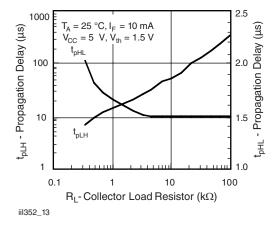


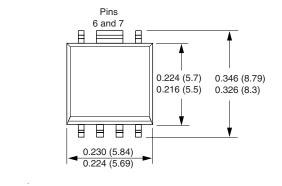
Fig. 13 - Propagation Delay vs. Collector Load Resistor

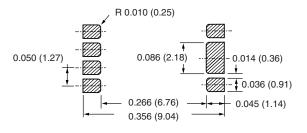
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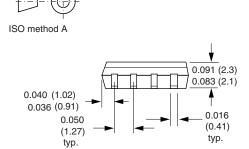
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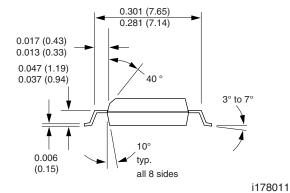


PACKAGE DIMENSIONS in inches (millimeters)











Optocoupler, Phototransistor Output, with Base Connection

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OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany





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